

Silicon NPN Power Transistors

2SC3692

DESCRIPTION

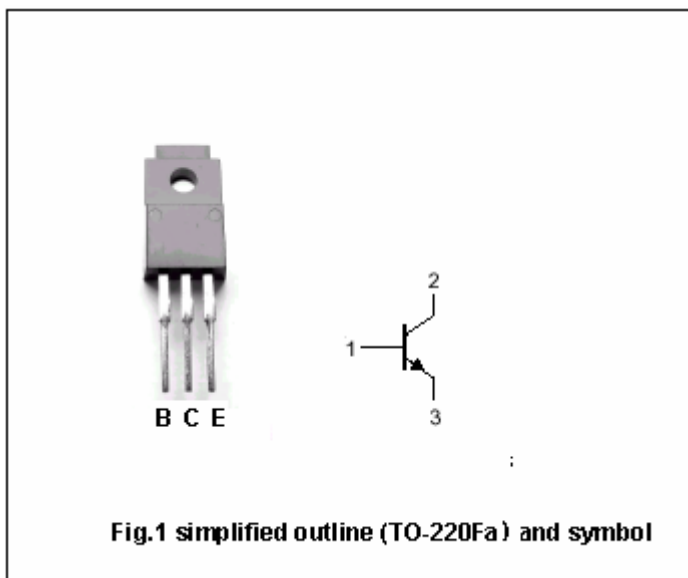
- With TO-220Fa package
- High DC current gain
- Low collector saturation voltage

APPLICATIONS

- For use in drivers such as DC/DC Converters and actuators

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7	A
I _{CM}	Collector current-peak		14	A
I _B	Base current		3.5	A
P _T	Total power dissipation	T _a =25	2.0	W
		T _C =25	30	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =4A; I _B =0.4A, L=1mH	60			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =4A; I _B =0.2 A			0.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =6A; I _B =0.3A			0.5	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =4A; I _B =0.2 A			1.2	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =6A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =60V; I _E =0			10	μA
I _{CEX}	Collector cut-off current	V _{CE} =60V; V _{BE} =-1.5V T _a =125			10 1.0	μA mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.7A; V _{CE} =2V	100			
h _{FE-2}	DC current gain	I _C =1.5A; V _{CE} =2V	100	200	400	
h _{FE-3}	DC current gain	I _C =4A; V _{CE} =2V	60			
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		100		pF
f _T	Transition frequency	I _C =1A; V _{CE} =10V		150		MHz

Switching times

t _{on}	Turn-on time	I _C =4A; R _L =12.5 I _{B1} =-I _{B2} =0.2A V _{CC} 50V			0.3	μs
t _s	Storage time				1.5	μs
t _f	Fall time				0.3	μs

◆ h_{FE-2} classifications

M	L	K
100-200	150-300	200-400

PACKAGE OUTLINE

